



2SK60

Silicon N-Channel Junction V-FET

- オーディオパワーアンプ
- HiFi: Power Amplifiers
- Complementary to 2SJ18

絶対最大定格 Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Characteristics	Symbol	2SK60
Drain-to-Gate Voltage	V_{DGO}	170V
Source-to-Gate Voltage	V_{SGO}	*1
Drain Current	I_D	5A
Gate Current	I_G	0.5A
Total Power Dissipation	P_T	63W ($T_c = 25^\circ\text{C}$)
Junction Temperature	T_j	120°C
Storage Temperature	T_{stg}	-50~+150°C

*1 Source-to-Gate Voltage V_{SGO} 2SK60-2

-3	}	-30V
-4		
-5		-35V
-6		-40V
-7		-45V
-8		-50V

電気的特性 Electrical Characteristics $T_a = 25^\circ\text{C}$

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain Cutoff Current	I_{DGO}	$V_{DG} = 100\text{V}$, $I_S = 0$		0.1	100	μA
Source Cutoff Current	I_{SGO}	$V_{GS} = 30\text{V}$, $I_D = 0$		0.1	100	μA
Drain-to-Source On-State Voltage	V_{on}	$I_G = 0.2\text{A}$, $I_D = 3\text{A}$, $t = 100\text{ms}$			10	V
Pinch-off Voltage	V_p	$V_{DS} = 60\text{V}$, $I_D = 100\text{mA}$	-7.5	-18	-25	V
Input Capacitance	C_{iss}	$V_{DS} = -15\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		190		pF
Gain Bandwidth Product	f_T	$V_{DS} = 20\text{V}$, $I_D = 0.5\text{A}$		20		MHz
Voltage Amplification Ratio	μ	$V_{DS} = 20\text{V}$, $I_D = 1\text{A}$, $f = 1\text{kHz}$		4		
Output Resistance	r_D	$V_{DS} = 20\text{V}$, $I_D = 1\text{A}$, $f = 1\text{kHz}$		16		Ω
Area of Safe Operation	ASO	$V_{DS} = 50\text{V}$, $t = 100\text{ms}$, $T_c = 25^\circ\text{C}$	2.5			A
Junction-to-Case Thermal Resistance	θ_{j-c}				1.5	$^\circ\text{C/W}$

